TRANSISTOR MOS-FET IGBT DIODE

$\triangle V_{BE}$/$\triangle V_{DS}$/$\triangle V_{GE}$/$\triangle V_{CE}$/$\triangle V_{F}$ TESTER 過渡熱抵抗測定器

DVFN1010Z

1000V 100A

NEW

●DVFN1010Z is the renewal model of 100V, 100A type which has used at research section or evaluation section. Long time forcing of 999sec is possible at 39.9A setting.

●従来より、研究開発部門や評価部門などで多く導入されてきた1000V, 100Aタイプのリニューアルモデルです。39.9A設定では999secの長時間印加が可能です。

MODEL	DVFN1010Z	
MEASUREMENT RANGE		
PRE-TEST	V_{BE1}/V_{DS1}/V_{GE1}/V_{CE1}/V_{F1}	0000mV~9999mV
	ΔV_{BE}/ΔV_{DS}/ΔV_{GE}/ΔV_{CE}/ΔV_{F}	0000mV~1999mV
MEASURABLE DEVICES		
	NPN/PNP, N/P-MOS FET, N/P-DIODE, N/P-IGBT(GE), N/P-IGBT(CE)	
SETTING RANGE	[TRANSISTOR, MOS-FET, IGBT]	
V_{CB}/V_{DS}	1V~999V	
I_{E}/I_{D}	0.01A~199.9A	
I_{M}	1mA~399mA	
POWER FORCING TIME(PT)	100µs~999s	
DELAY TIME(DT)	10µs~999µs	
GATE LIMIT(GL)	1.0V~19.9V	
LOWER GATE(LG)/UPPER GATE(UG)	0000mV~1999mV	
BINNING		
OPEN/SHORT CHECK	$V_{F1}>4V$…OPEN $V_{F1}<0.2V$…SHORT	
BIN INDICATION	PASS, LOW, HIGH, AVAL, REJECT	
DIMENSIONS & WEIGHT	550(W)×860(D)×1700(H)…380kg	

Forcing Power Range Diagram